

ABSTRACT

The invention ~~aims to provide~~ provides a semiconductor device and a method for manufacturing the same that are capable of improving the product performance and operational efficiency of a cross-point FeRAM. An upper electrode supporting layer forming ~~mask M1~~ mask for forming an upper electrode supporting ~~layer 2C~~ layer ~~can be made~~ of a hard mask material. By making use of the upper electrode supporting layer forming ~~mask M1~~ mask remaining unremoved in forming and processing a lower electrode ~~layer 2A~~ layer, prior to forming an upper electrode ~~layer 2D~~ layer, a region where a ferroelectric ~~capacitor C~~ capacitor is formed ~~is can be made~~ larger than an area occupied by an intersection of the upper electrode ~~layer 2D~~ layer and the lower electrode ~~layer 2A~~ layer.